

CBR35-010P SERIES

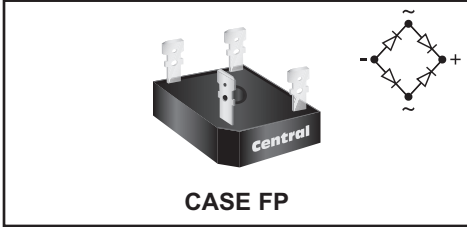
**SILICON BRIDGE RECTIFIERS
35 AMP, 100 THRU 1000 VOLT**



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DESCRIPTION:

The CENTRAL SEMICONDUCTOR CBR35-010P series devices are silicon, single phase, full wave bridge rectifiers designed for general purpose applications. The molded epoxy case has a built-in metal baseplate for heat sink mounting. The device utilizes standard 0.25" FASTON terminals.



CASE FP

MARKING: FULL PART NUMBER

MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$ unless otherwise noted)

		CBR35						
	SYMBOL	-010P	-020P	-040P	-060P	-080P	-100P	UNITS
Peak Repetitive Reverse Voltage	V_{RRM}	100	200	400	600	800	1000	V
DC Blocking Voltage	V_R	100	200	400	600	800	1000	V
RMS Reverse Voltage	$V_{R(RMS)}$	70	140	280	420	560	700	V
Average Forward Current ($T_C=60^\circ\text{C}$)	I_O				35			A
Peak Forward Surge Current	I_{FSM}				400			A
I^2t Rating for Fusing ($1\text{ms} < t < 8.3\text{ms}$)	I^2t				660			A^2s
RMS Isolation Voltage (case to lead)	V_{iso}				2500			Vac
Operating and Storage Junction Temperature	T_J, T_{stg}				-65 to +150			$^\circ\text{C}$
Thermal Resistance	θ_{JC}				1.4			$^\circ\text{C/W}$

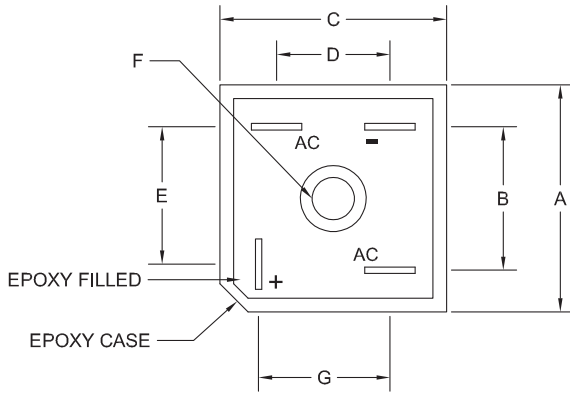
ELECTRICAL CHARACTERISTICS PER DIODE: ($T_A=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	TYP	MAX	UNITS
I_R	$V_R = \text{Rated } V_{RRM}$		10	μA
I_R	$V_R = \text{Rated } V_{RRM}, T_A = 125^\circ\text{C}$		500	μA
V_F	$I_F = 17.5\text{A}$		1.2	V
C_J	$V_R = 4.0\text{V}, f = 1.0\text{MHz}$	300		pF

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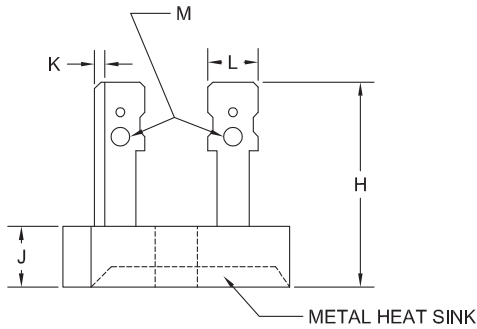
CASE FP - MECHANICAL OUTLINE



SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	1.115	1.135	28.32	28.83
B	0.688	0.732	17.50	18.59
C	1.115	1.135	28.32	28.83
D	0.542	0.582	13.77	14.78
E	0.618	0.672	15.70	17.07
F (DIA.)	0.200	0.220	5.08	5.59
G	0.632	0.672	16.05	17.07
H	0.740	0.849	18.80	21.58
J	0.290	0.334	7.37	8.50
K	0.027	0.035	0.71	0.91
L	0.250		6.35	
M (DIA.)	0.940		2.39	

CASE FP (REV:R2)

MARKING: FULL PART NUMBER



R2

R3 (24-June 2013)